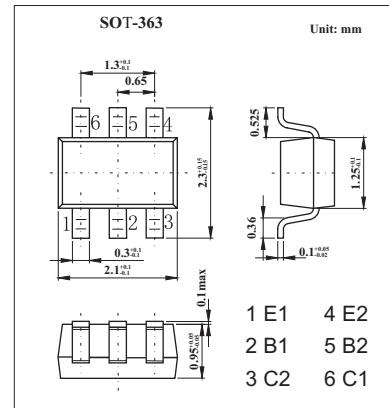
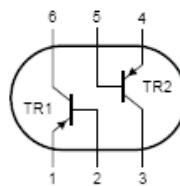


PNP General Purpose Double Transistor

KC856S(BC856S)

■ Features

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors.



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Rating | Unit |
|--------------------------------------------------|-----------------------------------|-------------|------|
| Collector-Base Voltage | V _{CB0} | -80 | V |
| Collector-Emitter Voltage | V _{C0E} | -65 | V |
| Emitter-Base Voltage | V _{E0B} | -5 | V |
| Collector Current - Continuous | I _C | -100 | mA |
| Power Dissipation | P _D | 200 | mW |
| Thermal Resistance, Junction to Ambient | R _{θ JA} | 416 | °C/W |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to +150 | °C |

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|--------------------------------------|-----------------------|-----------------------------------------------------------------------|-----|-----|------|------|
| Collector-Cutoff Current | I _{CB0} | V _{CB} = - 30 V, I _E = 0 | | | -15 | nA |
| | | V _{CB} = - 30 V, I _E = 0, T _A = 150 °C | | | -5.0 | μ A |
| Emitter- cutoff current | I _{E0B} | I _C =0, V _{EB} =-5V | | | -100 | nA |
| DC Current Gain | h _{FE} | I _C = -2.0 mA, V _{CE} = -5.0 V | 110 | | | |
| Collector-Emitter Saturation Voltage | V _{C0E(sat)} | I _C = -10 mA, I _B = - 0.5 mA | | | -100 | mV |
| | | I _C = -100 mA, I _B = - 5.0 mA | | | -300 | mV |
| Base-Emitter Saturation Voltage | V _{B0E(sat)} | I _C = -10 mA, I _B = - 0.5mA | | 700 | | m V |
| Output Capacitance | C _{ob} | V _{CB} = -10 V, f = 1.0 MHz | | | 2.5 | pF |
| Transistion frequency | f _T | I _C = -10 mA, V _{CE} = -5.0V, f = 100 mHz | 100 | | | MHz |

■ Marking

| | |
|---------|----|
| Marking | 5F |
|---------|----|